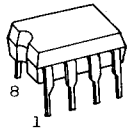
TC40107BP

TC40107BP DUAL 2-INPUT NAND BUFFER/DRIVER

TC40107BP is a dual 2-input NAND gate, of which output is of open-drain structure by use of N-channel MOS FET. Being capable of driving a large current, it can be directly connected to a relay, a lamp, a light-emitting diode (LED), etc. Wired OR can be also made.
(I_{OL}=74mA(Typ.) at V_{DD}=10V and V_{OL}=0.5V)
The package is a compact DIP 8-pin unit, which is easily mounted.
Since its output current is large, if the capacitor of an output line exceeds 500pF, a resistor of 25Ω or more should be used in series with the capacitor.

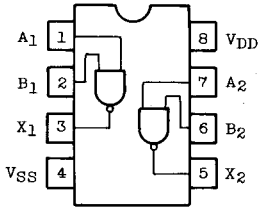


DIP 8(3D8A-P)

MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	RATING	UNIT
DC Supply Voltage	V_{DD}	V_{SS}-0.5 ~ V_{SS}+20	V
Input Voltage	V_{IN}	V_{SS}-0.5 ~ V_{DD}+0.5	V
Output Voltage	V_{OUT}	V_{SS}-0.5 ~ V_{DD}+0.5	V
DC Input Current	I_{IN}	±10	mA
Max. GND Current	I_{SS}	125	mA
Power Dissipation	P_D	300	mW
Operating Temperature Range	T_A	-40 ~ 85	°C
Storage Temperature Range	T_{stg}	-65 ~ 150	°C
Lead Temp./Time	T_{sol}	260°C · 10 sec	

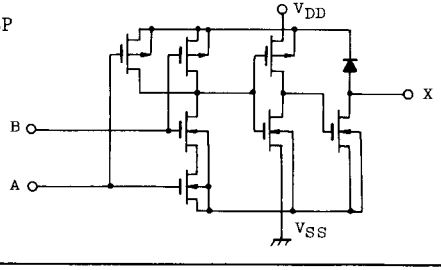
PIN ASSIGNMENT



(TOP VIEW)

CIRCUIT DIAGRAM

$\frac{1}{2}$ TC40107BP



TRUTH TABLE

INPUT		OUTPUT
A	B	X
L	L	HZ
L	H	HZ
H	L	HZ
H	H	L

HZ : High impedance

RECOMMENDED OPERATING CONDITIONS (V_{SS}=0V)

CHARACTERISTIC	SYMBOL		MIN.	TYP.	MAX.	UNIT
DC Supply Voltage	V_{DD}		3	-	18	V
Input Voltage	V_{IN}		0	-	V_{DD}	V
Load Capacitance	C_L		-	-	500	pF

STATIC ELECTRICAL CHARACTERISTICS (V_{SS}=0V)

CHARACTERISTIC	SYM-BOL	TEST CONDITION	V_{DD} (V)	-40°C MIN.	-40°C MAX.	25°C MIN.	25°C TYP.	25°C MAX.	85°C MIN.	85°C MAX.	UNIT
Low-Level Output Voltage	V_{OL}	$\|I_{OUT}\|<1\mu A$ $V_{IH}=V_{DD}$	5	-	0.05	-	0.00	0.05	-	0.05	V
			10	-	0.05	-	0.00	0.05	-	0.05	
			15	-	0.05	-	0.00	0.05	-	0.05	
Output Low Current	I_{OL}	V_{OL}=0.4V	5	20	-	16	32	-	14	-	mA
		V_{OL}=1.0V	5	42	-	34	68	-	30	-	
		V_{OL}=0.5V	10	46	-	37	74	-	32	-	
		V_{OL}=1.0V	10	85	-	68	136	-	60	-	
		V_{OL}=0.5V	15	63	-	50	100	-	44	-	
		$V_{IH}=V_{DD}$									
Input High Voltage	V_{IH} *	V_{OUT}=0.5V, 4.5V	5	3.5	-	3.5	2.75	-	3.5	-	V
		V_{OUT}=1.0V, 9.0V	10	7.0	-	7.0	5.5	-	7.0	-	
		V_{OUT}=1.5V,13.5V	15	11.0	-	11.0	8.25	-	11.0	-	
		$\|I_{OUT}\|<1\mu A$									
Input Low Voltage	V_{IL} *	V_{OUT}=4.5V	5	-	1.5	-	2.25	1.5	-	1.5	
		V_{OUT}=9.0V	10	-	3.0	-	4.5	3.0	-	3.0	
		V_{OUT}=13.5V	15	-	4.0	-	6.75	4.0	-	4.0	
		$\|I_{OUT}\|<1\mu A$									
Input Current "H" Level	I_{IH}	V_{IH}=18V	18	-	0.1	-	10^{-5}	0.1	-	1.0	μA
Input Current "L" Level	I_{IL}	V_{IL}=0V	18	-	-0.1	-	-10^{-5}	-0.1	-	-1.0	
3-State Output Leakage Current	I_{DH}	V_{OH}=18V	18	-	2	-	10^{-4}	2	-	20	
Quiescent Device Current	I_{DD} **	$V_{IN}=V_{DD},V_{SS}$ Outputs Open	5	-	1	-	0.001	1	-	7.5	
			10	-	2	-	0.001	2	-	15	
			15	-	4	-	0.002	4	-	30	

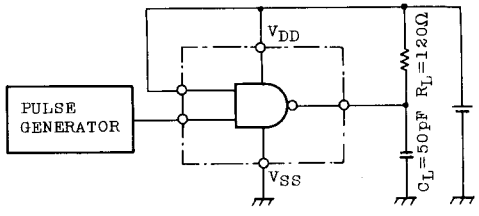
* Required external pull-up register R (=20kΩ)
** All valid input combinations.

DYNAMIC ELECTRICAL CHARACTERISTICS (Ta=25°C, V_{SS}=0V, C_L=50pF)

CHARACTERISTIC	SYMBOL	TEST CONDITION	V_{DD}(V)	MIN.	TYP.	MAX.	UNIT
Output Transition Time (Low to High)	t_{TLH}	R_L=120Ω	5	-	35	100	ns
			10	-	25	70	
			15	-	20	50	
Output Transition Time (High to Low)	t_{THL}	R_L=120Ω	5	-	35	100	ns
			10	-	10	40	
			15	-	7	20	
Propagation Delay Time (Low to High)	t_{pLH}	R_L=120Ω	5	-	60	200	ns
			10	-	35	120	
			15	-	30	100	
Propagation Delay Time (High to Low)	t_{pHL}	R_L=120Ω	5	-	70	200	ns
			10	-	30	90	
			15	-	20	60	
Input Capacitance	C_{IN}			-	5	7.5	pF
Output Capacitance	C_{OUT}			-	30	-	pF

CIRCUIT AND WAVEFORM FOR MEASUREMENT OF DYNAMIC CHARACTERISTICS

CIRCUIT



WAVEFORM